

Monolayer MoS₂ Growth at Au-SiO₂ Interface

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Supplementary Figures

Figure S1. Topographic images of the MoS₂ sheet. (a) Topographic image of the MoS₂ sample in Fig. 2b, and (b) magnified view of region outlined in (a). Yellow line in (b) indicates where the spatial topographic height profile in (c) was extracted.

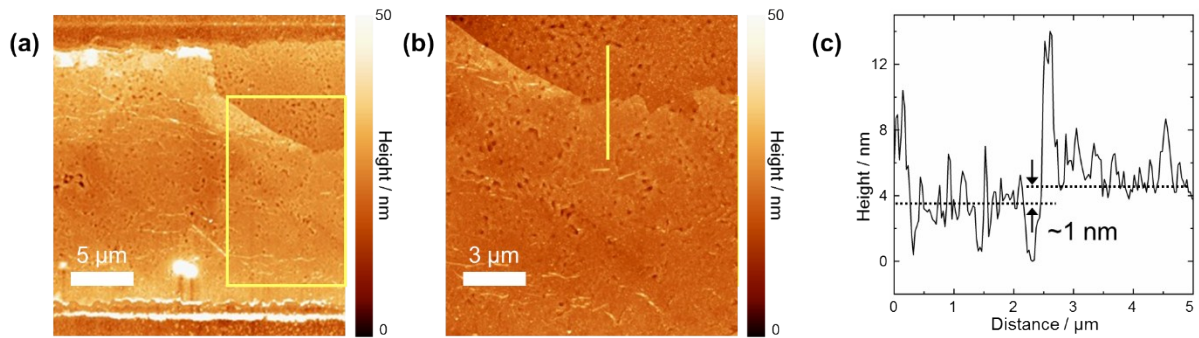


Figure S2. Cross-sectional TEM images of Au blocks. (a, b) Au blocks after CVD reaction at different locations. Scale bars are 500 nm.

